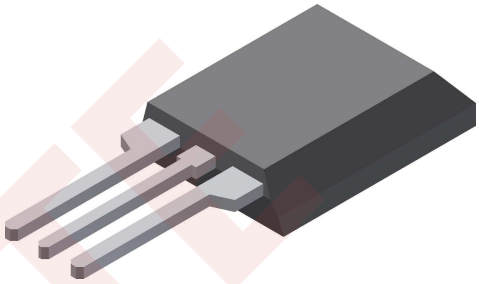
HiPerFRED

V_{RRM} = 2x 600 V
I_{FAV} = 15 A
t_{rr} = 25 ns

High Performance Fast Recovery Diode
Low Loss and Soft Recovery
Phase leg

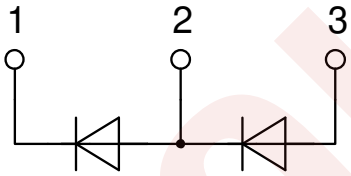
Part number

DSEE15-12CC



Backside: isolated

E72873



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low Irm-values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low Irm reduces:
  - Power dissipation within the diode
  - Turn-on loss in the commutating switch

Applications:

- Antiparallel diode for high frequency switching devices
- Antisaturation diode
- Snubber diode
- Free wheeling diode
- Rectifiers in switch mode power supplies (SMPS)
- Uninterruptible power supplies (UPS)

Package: ISOPLUS220

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

Disclaimer Notice

Information furnished is believed to be accurate and reliable. However, users should independently evaluate the suitability of and test each product selected for their own applications. Littelfuse products are not designed for, and may not be used in, all applications. Read complete Disclaimer Notice at www.littelfuse.com/disclaimer-electronics.

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Fast Diode

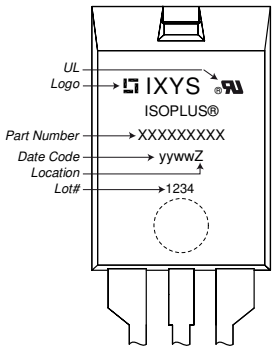
Symbol	Definition	Conditions		Ratings min.	typ.	max.	Unit
V_{RSM}	*max. non-repetitive reverse blocking voltage*		T_{VJ} = 25°C			600	V
V_{RRM}	*max. repetitive reverse blocking voltage*		T_{VJ} = 25°C			600	V
I_R	*reverse current, drain current*	V_R = 600 V	T_{VJ} = 25°C			100	µA
		V_R = 600 V	T_{VJ} = 150°C			0.5	mA
V_F	*forward voltage drop*	I_F = 15 A	T_{VJ} = 25°C			2.04	V
		I_F = 30 A				2.25	V
		I_F = 15 A	T_{VJ} = 150°C			1.35	V
		I_F = 30 A				1.59	V
I_{FAV}	*average forward current*	T_C = 140°C	T_{VJ} = 175°C			15	A
		rectangular d = 0.5					
V_{F0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 175°C			0.99	V
r_F	*slope resistance* }					15	mΩ
R_{thJC}	*thermal resistance junction to case*					1.6	K/W
R_{thCH}	*thermal resistance case to heatsink*				0.5		K/W
P_{tot}	*total power dissipation*		T_C = 25°C			95	W
I_{FSM}	*max. forward surge current*	t = 10 ms; (50 Hz), sine; V_R = 0 V	T_{VJ} = 45°C			110	A
C_J	*junction capacitance*	V_R = 400 V f = 1 MHz	T_{VJ} = 25°C		12		pF
I_{RM}	*max. reverse recovery current*		T_{VJ} = 25°C		11		A
		I_F = 15 A; V_R = 300 V	T_{VJ} = 100°C		19		A
t_{rr}	*reverse recovery time*	$-di_F/dt$ = 600 A/µs	T_{VJ} = 25°C		25		ns
			T_{VJ} = 100°C		83		ns

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Package ISOPLUS220				Ratings			
Symbol	**Definition**	**Conditions**		**min.**	**typ.**	**max.**	**Unit**
I_{RMS}	*RMS current*	per terminal				35	A
T_{VJ}	*virtual junction temperature*			-55		175	°C
T_{op}	*operation temperature*			-55		150	°C
T_{stg}	*storage temperature*			-55		150	°C
Weight					2		g
F_C	*mounting force with clip*			20		60	N
$d_{Spp/App}$	*creepage distance on surface | striking distance through air*		*terminal to terminal*	1.0			mm
$d_{Spb/Apb}$			*terminal to backside*	3.0			mm
V_{ISOL}	*isolation voltage*	t = 1 second	50/60 Hz, RMS; I_{ISOL} ≤ 1 mA	3600			V
		t = 1 minute		3000			V

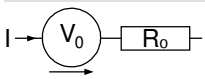
Product Marking



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSEE15-12CC	DSEE15-12CC	Tube	50	500725

Equivalent Circuits for Simulation

** on die level* T_{VJ} = 175°C

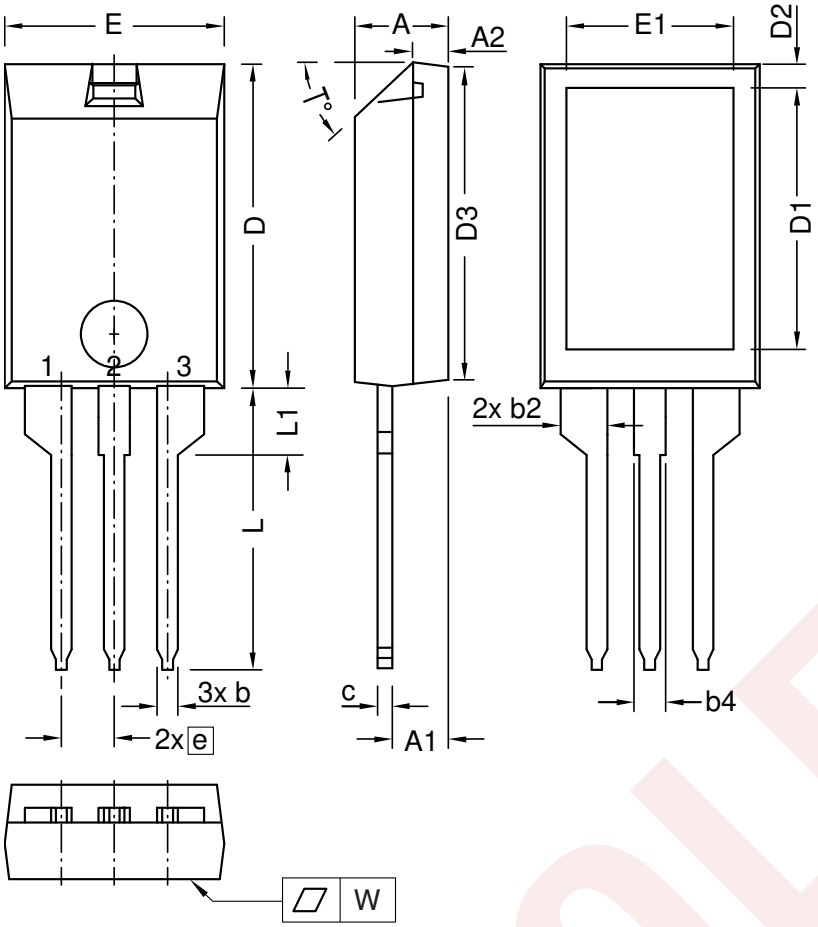


		Fast Diode	
$V_{0\ max}$	*threshold voltage*	0.99	V
$R_{0\ max}$	*slope resistance **	11.3	mΩ

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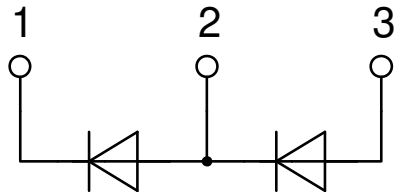
Outlines ISOPLUS220



Dim.	Millimeters		Inches	
	min	max	min	max
A	4.00	5.00	0.157	0.197
A1	2.50	3.00	0.098	0.118
A2	1.60	1.80	0.063	0.071
b	0.90	1.30	0.035	0.051
b2	2.20	2.55	0.087	0.100
b4	1.25	1.65	0.049	0.065
c	0.70	1.00	0.028	0.039
D	15.00	16.00	0.591	0.630
D1	12.00	13.00	0.472	0.512
D2	1.10	1.50	0.043	0.059
D3	14.90	15.50	0.587	0.610
E	10.00	11.00	0.394	0.433
E1	7.50	8.50	0.295	0.335
e	2.54 BSC		0.100 BSC	
L	13.00	14.50	0.512	0.571
L1	3.00	3.50	0.118	0.138
T°	42.5	47.5		
W	-	0.1	-	0.004

Die konvexe Form des Substrates ist typ. < 0.04 mm über der Kunststoffoberfläche der Bauteilunterseite
The convex bow of substrate is typ. < 0.04 mm over plastic surface level of device bottom side

Die Gehäuseabmessungen entsprechen dem Typ TO-273 gemäß JEDEC außer D und D1.
This drawing will meet all dimensions requiarement of JEDEC outline TO-273 except D and D1.



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Fast Diode

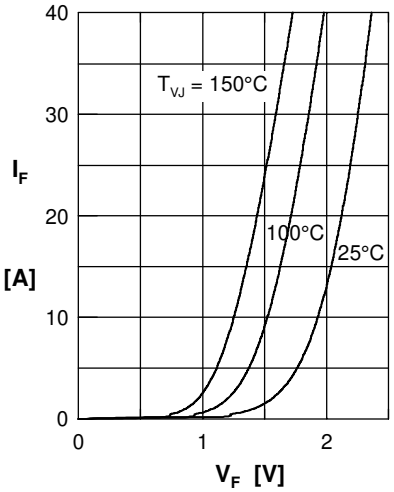


Fig. 1 Forward current I_F vs. V_F

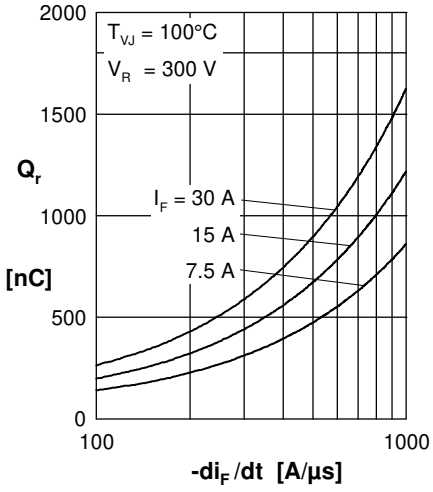


Fig. 2 Typ. reverse recovery charge Q_{rr} versus $-di_F/dt$

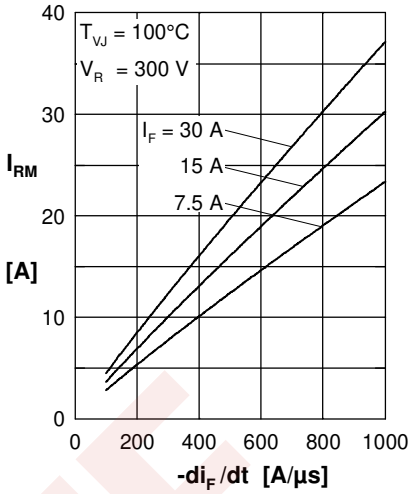


Fig. 3 Typ. peak reverse current I_{RM} versus $-di_F/dt$

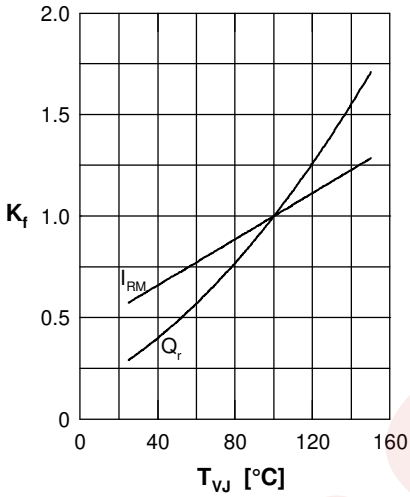


Fig. 4 Dynamic parameters Q_r, I_{RM} versus T_{VJ}

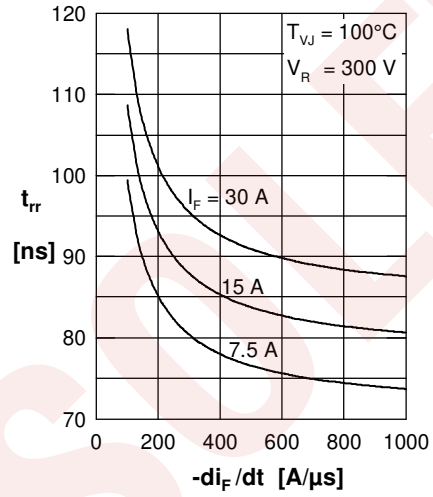


Fig. 5 Typ. recovery time t_{rr} versus $-di_F/dt$

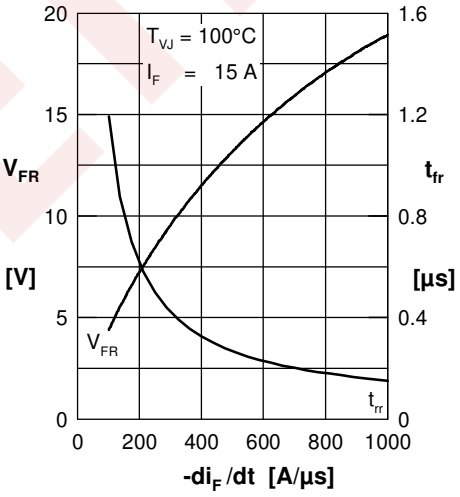


Fig. 6 Typ. peak forward voltage V_{FR} and typ. forward recovery time t_{fr} versus di_F/dt

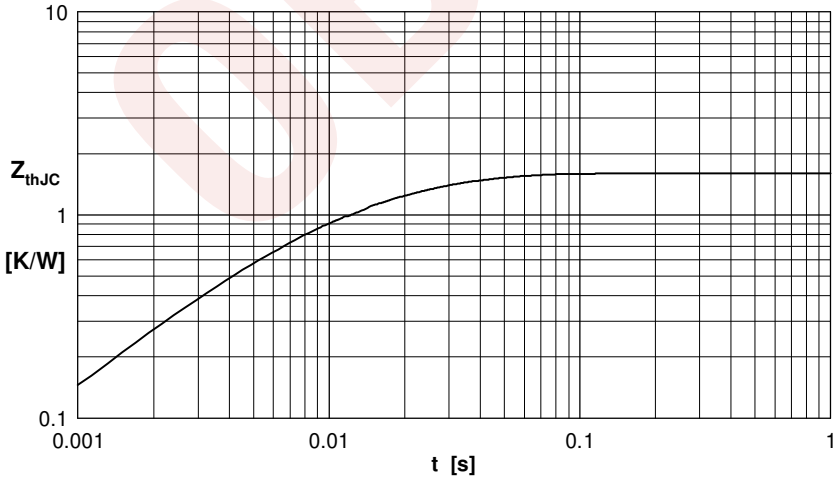


Fig. 7 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} [K/W]	t_i [s]
1	0.908	0.0052
2	0.350	0.0003
3	0.342	0.0170

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